Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-37. (Canceled)

38. (Previously Presented) The patterning method according to claim 70, the first liquid material being the same as the second liquid material.

39. (Previously Presented) The patterning method according to claim 70, the first liquid material being different from the second liquid material.

40-44. (Canceled)

45. (Currently Amended) The patterning method according to claim 74 wherein the ~~plurality of indents are~~ secondary barrier is provided with a castellated cross-sectional profile.

46. (Currently Amended) The patterning method according to claim 74 wherein the ~~plurality of indents are~~ secondary barrier is provided with a saw-tooth cross-sectional profile.

47. (Currently Amended) The patterning method according to claim 74 ~~comprising providing~~ wherein the plurality of indents include first and second indent regions of elongate shape and ~~impressing~~ a further elongate indent region is arranged between but spaced from the first and second indent regions, the further elongate indent region having a substantially planar bottom surface.

48. (Previously Presented) A method of manufacturing an electronic device, the method comprising:

making a pattern by the patterning method according to claim 70.

49. (Currently Amended) The method of manufacturing an electronic device according to claim ~~48,~~ 48 wherein the first liquid material ~~including~~ includes a

semiconductor material, and the second liquid material ~~including~~ includes a semiconductor material.

50. (Currently Amended) The method of manufacturing an electronic device according to claim ~~49,~~ 49 wherein a source of a transistor is formed between the at least one of a plurality of indents and a second indent of the plurality of indents, and a drain of the transistor ~~being~~ is formed ~~in a first part between a first indent of the plurality of indents, and a second part between the first indent and a third indent of the plurality of indents, respectively;~~ between the at least one of a plurality of indents and a third indent of the plurality of indents, and a channel of the transistor being formed between the first part and the second part.

51. (Currently Amended) A patterning method comprising:

forming an indent region in the surface of a substrate; and

depositing a liquid material onto the surface at selected locations adjacent to the indent region such that spread of the liquid material over the surface is ~~controlled~~ repelled by an edge of the indent ~~region;~~ region,

wherein the indent region is formed with a cross-sectional profile to provide a secondary barrier within the indent region to further ~~control~~ repel the spread of the material ~~over the surface~~; and

wherein the material is selected to ~~comprise~~ form a semiconductor material and the selected locations ~~comprise the surface~~ are between ~~elongate~~ the indent region and an adjacent indent ~~regions~~ region so as to provide source and drain regions for a thin film transistor having a channel length determined by ~~the~~ a width of ~~further elongate~~ the indent ~~regions~~ region and a channel width determined by ~~the~~ a length of the ~~further elongate~~ indent region.

52-58. (Canceled)

59. (Currently Amended) A patterning method for depositing a liquid onto a surface of a ~~substrate;~~ substrate, said method comprising:

forming a first and second indent in the surface of the substrate, each indent having falling edges co-incident with the surface and spaced a distance apart, ~~and in which forming~~ the first and second indents ~~includes forming~~ including wall portions sloping relative to the surface, the falling edges repel spreading of the liquid into the indents;

depositing said liquid between and adjacent to said indents; and

selecting the distance between the falling edges such that a greater volume of liquid is deposited and retained than in the absence of at least one of the indents.

60. (Currently Amended) A method of manufacturing an electronic device, the method further comprising:

making a pattern by the patterning method according to claim 59.

61. (Canceled)

62. (Currently Amended) A patterning method for depositing a liquid onto a surface of a substrate, said method comprising:

forming a first and second indent in the surface of the substrate, each indent having falling edges co-incident with the surface and spaced a distance apart, ~~and in which forming~~ the first and second indents ~~includes forming~~ including wall portions sloping relative to the surface, the falling edges repel spreading of the liquid into the indents;

depositing said liquid between and adjacent to said indents; and

selecting the distance between the falling edges such that a greater contact angle between the liquid and the surface is provided than in the absence of at least one of the indents.

63. (Previously Presented) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to claim 62.

64. (Canceled)

65. (Currently Amended) A patterning method for depositing a liquid onto a surface of a substrate, said method comprising:

forming a first and second indent in the surface of the substrate, each indent having falling edges co-incident with the surface and spaced a distance apart, ~~and in which forming~~ the first and second indents ~~includes forming~~ including wall portions sloping relative to the surface, the falling edges repel spreading of the liquid into the indents;

depositing said liquid between and adjacent to said indents; and

selecting the distance between the falling edges such that ~~the~~ a diameter of the deposited liquid is greater than the distance between the falling edges.

66. (Previously Presented) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to claim 65.

67. (Canceled)

68. (Currently Amended) A patterning method for depositing a liquid onto a surface of a substrate, said method comprising:

forming a first and second indent in the surface of the substrate, each indent having falling edges co-incident with the surface and spaced a distance apart, ~~and in which forming~~ the first and second indents ~~includes forming~~ including wall portions sloping relative to the surface, the falling edges repel spreading of the liquid into the indents;

depositing said liquid between and adjacent to said indents; and

selecting the distance between the falling edges such that ~~the~~ a thickness of the liquid deposited and retained on the surface of the substrate is greater than in the absence of at least one of the indents.

69. (Previously Presented) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to claim 68.

70. (Currently Amended) A patterning method, comprising:

depositing a first liquid material on a substrate surface adjacent to a first side of a plurality of indents formed in the substrate surface; and

depositing a second liquid material on ~~a~~ the substrate surface adjacent to a second side of the plurality of indents,

~~a plurality of indents being formed in the substrate, and~~

~~the plurality of indents being formed between the first liquid material deposited by the depositing of the first liquid material and the second liquid material deposited by the depositing of the second liquid material.~~ the first and second sides of the plurality of indents having edges that repel spreading of the first and second liquid materials into the plurality of indents.

71. (Currently Amended) A patterning method, comprising:

depositing a first liquid material on a substrate surface adjacent to a first side of an indent formed in the substrate surface; and

depositing a second liquid material on ~~a~~ the substrate surface adjacent to a second side of the indent,

~~an indent being formed in a surface of the substrate, and~~

~~the indent being formed between the first liquid material deposited by the depositing of the first liquid material and the second liquid material deposited by the depositing of the second liquid material, and~~each of the first and second sides of the indent having an edge that repels spreading of the first and second liquid materials into the indent,

the indent ~~has~~ having a width tapering towards ~~the~~ a bottom.

72. (Currently Amended) A patterning method, comprising:

depositing a first liquid material on a substrate surface adjacent to a first side of an indent formed in the substrate surface; and

depositing a second liquid material on ~~a~~ the substrate surface adjacent to a second side of the indent,

~~an indent being formed in a surface of the substrate, and~~

~~the indent being formed between the first liquid material deposited by the depositing of the first liquid material and the second liquid material deposited by the depositing of the second liquid material, and~~each of the first and second sides of the indent having an edge that repels spreading of the first and second liquid materials into the indent,

the indent ~~has~~ having a width widening towards ~~the~~ a bottom.

73. (Currently Amended) A patterning method according to claim 70, each of the plurality of indents having wall portions which have slopes relative to ~~a surface of a~~ the surface of the substrate.

74. (Currently Amended) The patterning method according to claim ~~73,~~ 70, the plurality of indents being formed with a cross-sectional profile ~~to~~ including a secondary barrier to control ~~spread~~ spreading of the first liquid material and the second liquid material.

75. (Currently Amended) The patterning method according to claim 70, further comprising:

adjusting a wetting characteristic of ~~a~~ the surface of the substrate relative to the first liquid material and the second liquid material.

76. (Previously Presented) The patterning method according to claim 70, each of the plurality of indents having a substantially planar bottom surface.

77. (Currently Amended) The patterning method according to claim 70, further comprising forming the plurality of indents by an impression technique.

78. (Previously Presented) The patterning method according to claim 77, the impression technique using at least one of a stamping die and a moulding technique.

79. (Previously Presented) The patterning method according to claim 70, the first liquid material including a conductive material.